

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	10	Higashi-seiichiro.inv.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/18 17:18
S1	78	(substrate adj temperature) and (interface adj level adj density)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/18 14:13
S2	2	(gate adj insulating adj film) with (interface adj level adj density) with (semiconductor adj layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/18 14:17
S3	0	(gate adj insulating adj layer) with (interface adj level adj density) with (semiconductor adj layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/18 14:17
S4	0	(gate adj oxide adj layer) with (interface adj level adj density) with (semiconductor adj layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/18 14:17
S5	1	(gate adj oxide adj film) with (interface adj level adj density) with (semiconductor adj layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/18 14:18
S6	1	(gate adj oxide) with (interface adj level adj density) with (semiconductor adj layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/18 14:18
S7	0	(gate adj insulator) with (interface adj level adj density) with (semiconductor adj layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/18 14:18
S8	2	(gate adj insulating) with (interface adj level adj density) with (semiconductor adj layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/18 14:19
S9	0	(gate adj insulative) with (interface adj level adj density) with (semiconductor adj layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/18 14:19

S10	0	(gate adj insulative) with (interface adj level adj density) with substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/18 14:19
S11	11	(gate adj insulat\$) with (interface adj level adj density) with substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/18 14:20
S12	7	(gate adj oxide) with (interface adj level adj density) with substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/18 14:21
S13	13	(gate adj oxide) same (interface adj level adj density) same substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/18 14:39
S14	38	(gate adj insulat\$) same (interface adj level adj density) same substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/18 14:45
S15	35	(gate adj insulat\$) same (interface adj level adj density) same semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/18 14:51
S16	42	(gate adj insulat\$) with (interface adj level adj density)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/18 14:54
S17	24	(gate adj oxide) with (interface adj level adj density)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/18 14:58
S18	277	(interface adj level adj density)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/18 16:07
S19	29	(heat adj treating) with (atmosphere adj containing adj water)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/18 15:40

S20	29	(heat adj treating) same (atmosphere adj containing adj water)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/18 15:40
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